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XP5501

Silicon NPN epitaxial planer transistor

For general amplification

Features

- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

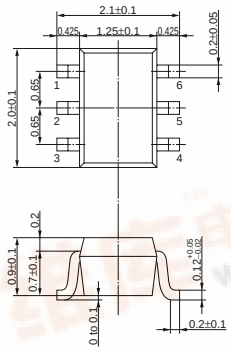
Basic Part Number of Element

- 2SD601A × 2 elements

Absolute Maximum Ratings (Ta=25˚C)

Parameter		Symbol	Ratings	Unit
Rating of element	Collector to base voltage	V_{CBO}	60	V
	Collector to emitter voltage	V_{CEO}	50	V
	Emitter to base voltage	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Overall	Total power dissipation	P_T	150	mW
	Junction temperature	T_j	150	˚C
	Storage temperature	T_{stg}	–55 to +150	˚C

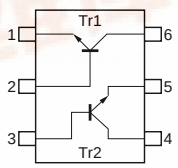
Unit: mm



1 : Emitter (Tr1)
2 : Base (Tr1)
3 : Base (Tr2)
4 : Collector (Tr2)
5 : Emitter (Tr2)
6 : Collector (Tr1)
EIAJ : SC–88
S–Mini Type Package (6–pin)

Marking Symbol: 5L

Internal Connection



Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	I_C = 10μA, I_E = 0	60			V
Collector to emitter voltage	V_{CEO}	I_C = 2mA, I_B = 0	50			V
Emitter to base voltage	V_{EBO}	I_E = 10μA, I_C = 0	7			V
Collector cutoff current	I_{CBO}	V_{CB} = 20V, I_E = 0			0.1	μA
	I_{CEO}	V_{CE} = 10V, I_B = 0			100	μA
Forward current transfer ratio	h_{FE}	V_{CE} = 10V, I_C = 2mA	160		460	
Forward current transfer h_{FE} ratio	h_{FE} (small/large)*1	V_{CE} = 10V, I_C = 2mA	0.5	0.99		
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 100mA, I_B = 10mA		0.1	0.3	V
Transition frequency	f_T	V_{CB} = 10V, I_E = –2mA, f = 200MHz		150		MHz
Collector output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz		3.5		pF

*1 Ratio between 2 elements

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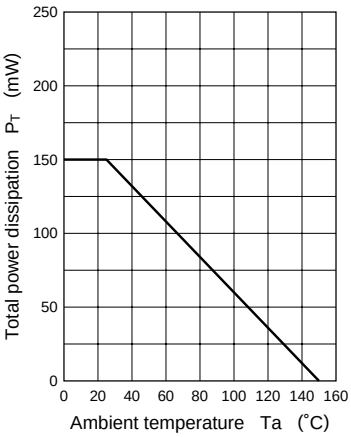
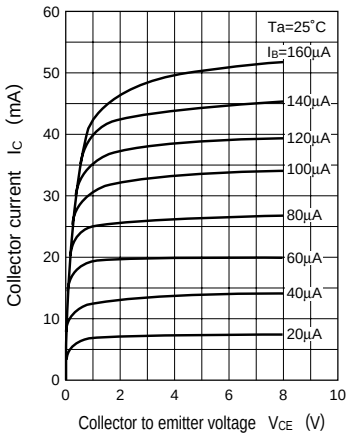
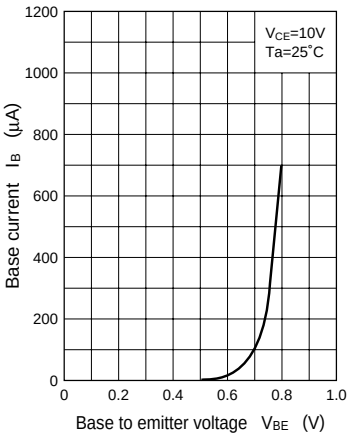
P_T — Ta



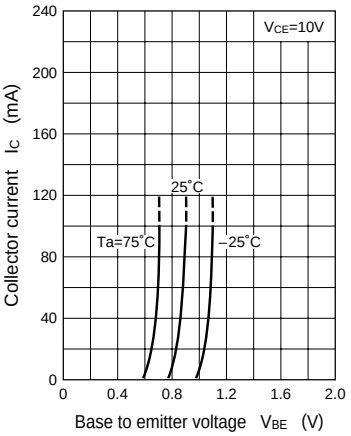
I_C — V_{CE}



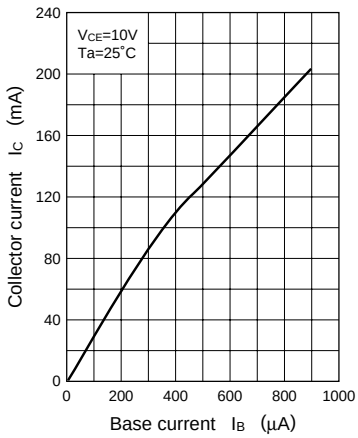
I_B — V_{BE}



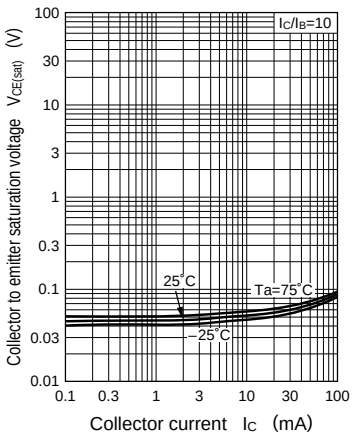
I_C — V_{BE}



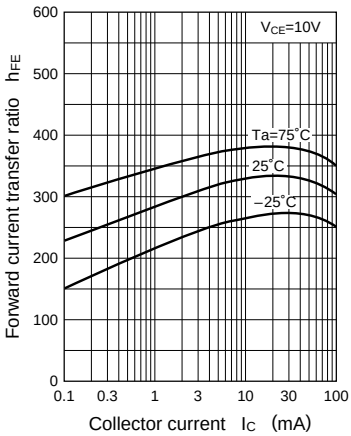
I_C — I_B



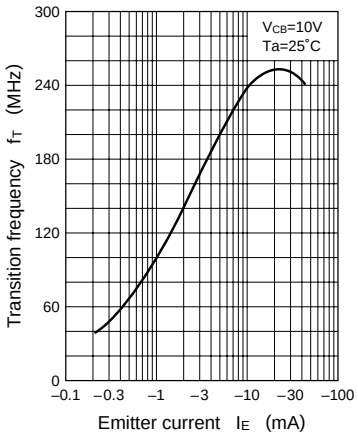
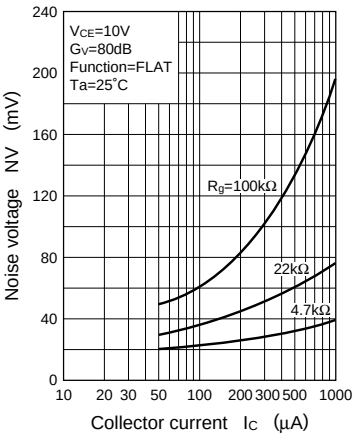
$V_{CE(sat)}$ — I_C



h_{FE} — I_C



f_T — I_E



NV — I_C